

DESCRIPTION

The MBD914 is available in SOT-23 Package.

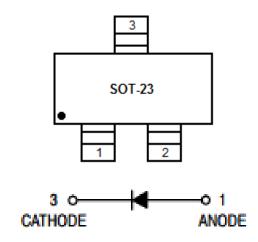
FEATURES

Available in SOT-23 Package

ORDERING INFORMATION

Package Type	e Part Number	
SOT-23	MBD914	
Note	SPQ: 3,000pcs/Reel	
AiT provides all RoHS Compliant Products		

PIN DESCRIPTION



REV1.0 - AUG 2015 RELEASED - -1-



ABSOLUTE MAXIMUM RATINGS

V _R , Reverse Voltage	100Vdc
I _F , Forward Current	200mAdc
I _{FM(surge)} , Peak Forward Surge Current	500mAdc

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, NOTE1			
T _A = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	Reja	556	°C/W
Total Device Dissipation Alumina SubstrateNOTE2			
T _A = 25°C	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	R _{0JA}	417	°C/W
Junction and Storage Temperature	TJ, T _{STG}	-55 ~ +150	°C

NOTE1: FR-5 = $1.0 \times 0.75 \times 0.062$ in.

NOTE2: Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS

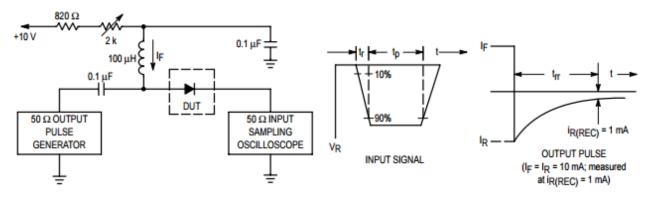
 $T_A = 25$ °C, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage	$V_{(BR)}$	I _R = 100μAdc	100	-	Vdc
Reverse Voltage Leakage Current	I_{R}	V _R = 20Vdc	-	25	nAdc
		V _R = 75Vdc	-	5.0	μAdc
Diode Capacitance	Ст	V _R = 0V, f = 1.0 MHz	-	4.0	pF
Forward Voltage	V _F I _F = 10mAdc		-	1.0	Vdc
Reverse Recovery Time	t _{rr}	$I_F = I_R = 10$ mAdc (Figure.1)	-	4.0	ns

REV1.0 - AUG 2015 RELEASED - - 2

TYPICAL PERFORMANCE CHARACTERISTICS

Figure. 1 Recovery Time Equivalent Test Circuit



NOTE1: A $2.0k\Omega$ variable resistor adjusted for a Forward Current (I_F) of 10mA.

NOTE2: Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.

NOTE3: t_p » t_{rr}

Figure. 2 Forward Voltage

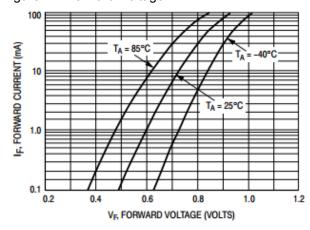


Figure. 3 Leakage Current

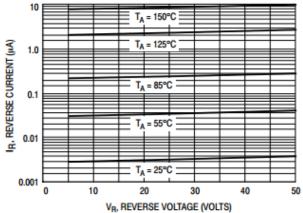
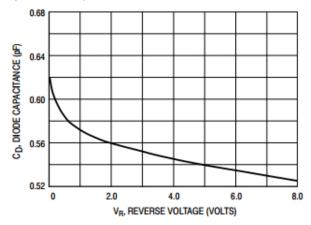


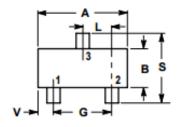
Figure. 4 Capacitance

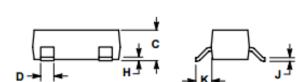


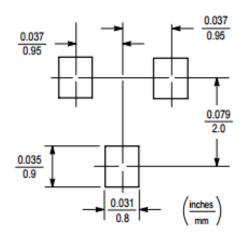
REV1.0 - AUG 2015 RELEASED - - 3 -

PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)







DIM	INCHES		MILLIMETERS		
	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
V	0.0177	0.0236	0.45	0.60	

REV1.0 - AUG 2015 RELEASED - - 4 -



IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc.'s integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or server property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.

REV1.0 - AUG 2015 RELEASED - - 5 -